

SKiiP 2414 GB17E4-4DPVW V2

Features*

- Intelligent Power Module
- Integrated current and temperature measurement
- · Integrated DC-link measurement
- · Solder free power section
- IGBT4 and CAL4F technology
- Safety isolated switching and sensor signals
- · Digital signal transmission
- · CAN Interface
- 100% tested IPM
- RoHS compliant
- UL file no. E242581

Typical Applications

- · Renewable energies
- Traction
- Elevators
- Industrial drives

Remarks

For further information please refer to SKiiP®4 Technical Explanation

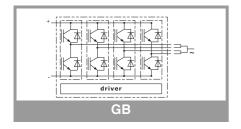
Footnotes

¹⁾With assembly of suitable MKP capacitor per terminal. For operation up to 1500V see Figure 11

 $^{2)}\bar{T}he$ specified maximum operation junction temperature T_{vjop} can be > 150°C for a max. of 1000cum. Operations hours

Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
System							
V _{CC} 1)	Operating DC link v	oltage	1300	V			
V _{isol}	DC, t = 1 s, each po	olarity	5600	V			
I _{t(RMS)}	per AC terminal, rm	s, sinusoidal current	500	Α			
I _{max (peak)}	max. peak current o	'	3600	Α			
I _{FSM}	$T_j = 175 ^{\circ}\text{C}, t_p = 10$	ms, sin 180°	15885	Α			
I ² t	$T_j = 175 ^{\circ}C, t_p = 10$	ms, diode	1262	kA ² s			
f_{out}	fundamental output (sinusoidal)	frequency	1	kHz			
T _{stg}	storage temperature	е	-40 85	°C			
IGBT							
V _{CES}	T _j = 25 °C		1700	V			
I _C	T _i = 175 °C	T _s = 25 °C	3385	Α			
	1, - 175 0	T _s = 70 °C	2723	Α			
I _{Cnom}			2400	Α			
$T_j^{2)}$	junction temperatur	e	-40 175	°C			
Diode							
V_{RRM}	T _j = 25 °C		1700	V			
I _F	T _i = 175 °C	$T_s = 25 ^{\circ}C$	2362	Α			
	11, = 175 0	T _s = 70 °C	1869	Α			
I _{Fnom}			2400	Α			
$T_j^{2)}$	junction temperature		-40 175 °C				
Driver							
V _s	power supply		19.2 28.8	V			
V_{iH}	input signal voltage	(high)	$V_{s} + 0.3$	V			
dv/dt	secondary to prima	ry side	75	kV/μs			
f_{sw}	switching frequency	/	10	kHz			

Characteristics							
Symbol	Conditions		min.	typ.	max.	Unit	
IGBT							
V _{CE(sat)}	I _C = 2400 A	T _j = 25 °C		2.12	2.43	V	
	at terminal	T _j = 150 °C		2.53	2.79	V	
V_{CE0}		T _j = 25 °C		1.10	1.20	V	
		T _j = 150 °C		1.00	1.10	V	
r _{CE}	at terminal	T _j = 25 °C		0.42	0.51	mΩ	
	at terriiriai	T _j = 150 °C		0.64	0.70	mΩ	
E _{on} + E _{off}	I _C = 2400 A	V _{CC} = 900 V		1780		mJ	
	T _j = 150 °C	V _{CC} = 1300 V		2840		mJ	
R _{th(j-s)}	per IGBT switch	•			0.0138	K/W	
R _{th(j-r)}	per IGBT switch				0.01	K/W	





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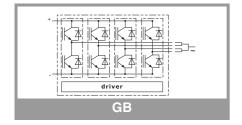
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Characte	ristics					
Symbol	Conditions		min.	typ.	max.	Unit
Diode			•			
$V_F = V_{EC}$	I _F = 2400 A	T _j = 25 °C		2.02	2.34	V
	at terminal	T _j = 150 °C		2.27	2.62	V
V_{F0}		T _j = 25 °C		1.21	1.36	V
		T _j = 150 °C		0.99	1.12	V
r _F	at terminal	T _j = 25 °C		0.34	0.41	mΩ
	attermina	T _j = 150 °C		0.53	0.63	mΩ
E _{rr}	I _F = 2400 A	V _R = 900 V		412		mJ
	T _j = 150 °C	V _R = 1300 V		664		mJ
$R_{th(j-s)}$	per diode switch				0.0281	K/W
$R_{th(j-r)}$	per diode switch				0.0241	K/W
Driver						
Vs	supply voltage non	stabilized	19.2	24	28.8	V
I _{S0}		24V, $f_{sw} = 0$, $I_{AC} = 0$		260		mA
Is	$k_1 = 46 \text{ mA/kHz}, k_2$ $f_{\text{out}} = 50 \text{Hz}, \text{ sinusoid}$		= 260	+ k ₁ * f _{sw}	+ k ₂ * I _{AC} ²	mA
$V_{\text{IT+}}$	input threshold volt	age (HIGH)	0,7*V _s			V
V _{IT-}	input threshold volt	age (LOW)			0,3*V _s	V
R _{IN}	input resistance			13		kΩ
C _{IN}	input capacitance		1		nF	
t _{pRESET}	error memory reset time			500		ms
$t_{pReset(OCP)}$	Over current reset time, FRT-function can be activated via CAN interface					μs
t _{TD}	top / bottom switch	interlock time		3		μs
t _{jitter}	jitter clock time			50	58	ns
t _{SIS}	short pulse suppres	ssion time		0.6		μs
t _{POR}	Power-On-Reset co	ompleted			1	S
I _{digiout}	digital output sink current (HALT-signal)				16	mA
V _{it+ HALT}	input threshold volt (Low>High)	age HIGH HALT	0,6*V _s			V
$V_{it\text{-HALT}}$	input threshold volt (High> Low)	input threshold voltage LOW HALT			0.4*V _s	V
t _{d(err)}	Error delay time (from detection to HALT), (depends on kind of error)		3		370	μs
I _{TRIPSC}	over current trip lev	rel .	3600			A _{PEAK}
I _{LL}				n.a.		A _{PEAK}
T _{trip}	over temperature tr	ip level	128	135	142	°C
$T_{DriverTrip}$	over temperature F	CB trip level	113	120	124	°C
V _{DCtrip}	over voltage trip lev	/el,		not impl.		V
V _{DCtripLL}				n.a.		٧





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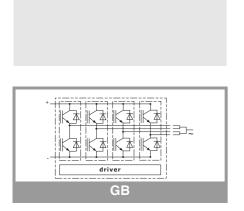
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 $^{2)}$ The specified maximum operation junction temperature $T_{\nu jop}$ can be > 150°C for a max. of 1000cum. Operations hours



Characteristics						
Symbol	Conditions	min.	typ.	max.	Unit	
System						
t _{d(on)IO}	V _{CC} = 1300 V I _C = 2400 A	turn on propagation delay time		2.8		μs
$t_{d(off)IO}$	$T_j = 25 ^{\circ}\text{C}$	turn off propagation delay time	2.6			μs
dV_{CE}/dt_{on}	T 05 °C	$I_C = 0 A$	14			kV/μs
	T _j = 25 °C V _{CC} = 1300 V	$I_C = 2400 \text{ A}$		3		kV/μs
dV_{CE}/dt_{off}		$I_C = 2400 \text{ A}$	10			kV/μs
R _{th(s-a)}	flow rate = 15 l/min, T _{Fluid} =40°C, water/glycol ratio 50%:50%				0.0065	K/W
R _{CC'+EE'}	measured per sv	neasured per switch, T _s = 25 °C		0.0675		mΩ
L _{CE}	commutation ind	uctance		4.5		nΗ
C _{CHC}	coupling capacitance secondary to heat sink		6		nF	
C _{ps}	coupling capacitance primary to secondary		0.08			nF
I _{CES} + I _{RD}	$V_{GE} = 0 \text{ V}, V_{CE} =$	1700 V, T _j = 25 °C	0.199			mA
M _{dc}	DC terminals		6		8	Nm
M _{ac}	AC terminals		13		15	Nm
w	SKiiP System w/o heat sink		3.22			kg
Wh	heat sink			4.25		kg

Isolation coordination acc. to EN 50178 and IEC 61800-5-1					
Maximum grid RMS voltage, line-to-line, grounded delta mains	690V+20%				
Installation altitude for maximum grid RMS voltage, line-to-line, grounded delta mains	2000m				
Maximum grid RMS voltage, line-to-line, star point grounded mains	690V+20%				
Installation altitude for maximum grid RMS voltage, line-to-line, star point grounded mains	4000m				
Maximum transient peak voltage between low voltage circuit and mains	1900V				
Pollution degree acc. to IEC 60664-1 outside the moulded power section	2				
Overvoltage cat. acc. to IEC 60664-1 for mains	III				
Overvoltage cat. acc. to UL 840 within mains	I				
Overvoltage cat. acc. to UL 840 between mains and ground	III				
Overvoltage cat. acc. to UL 840 between mains and low voltage circuit	III				
Basic isolation	between heat sink and mains				
Reinforced isolation	between low voltage circuit and mains				
Protection level acc. to IEC 60529	IP00				

Environmental conditions acc. to IEC 60721

	Storage	Transportation	Operation stationary use at weather protected locations	Operating ground vehicle installations	Operating ship environment
Climatic conditions	1K2 ₍₁₎	2K2 ₍₁₎	3K3 ₍₁₎	5K1 ₍₁₎	6K1 ₍₁₎
Biological conditions	1B1	2B1	3B1	5B1	6B1
Chemically active substances (excluded: salt spray)	1C2	2C1	3C2	5C2	6C2
Mechanically active substances	181	281	381	581	6S1
Mechanical conditions	1M3	(4)	3M6 ₍₂₎	5M3 ₍₃₎	6M3
Contaminating fluids				5F1	

- (1) expanded temperature range: -40°C / +85°C. Please note: by operation near 85°C the life time of product is reduced.
- (2) 3M7 possible, but due to the mechanic load capacity of external components like DC-Link capacitors limited to 3M6
- (3) 5M3 without impact of foreign bodies, stones
- (4) no declaration due to customer-specific packing

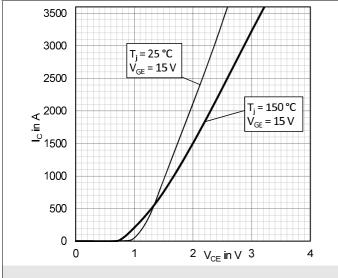


Fig. 1: Typical IGBT output characteristics

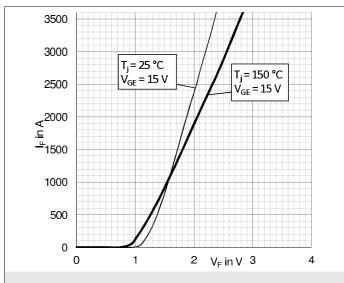


Fig. 2: Typical diode output characteristics

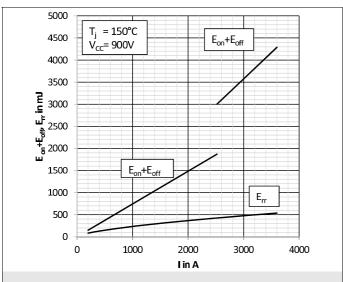


Fig. 3: Typical switching energy $E = f(I_c)$

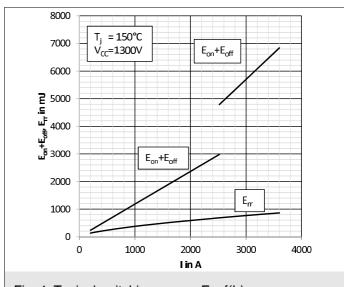
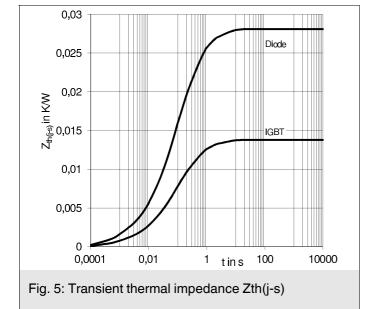
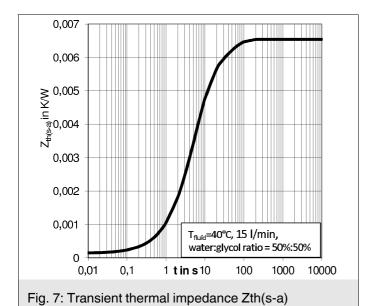


Fig. 4: Typical switching energy $E = f(I_c)$



0,03 Diode 0,025 0,02 Z_{tr(g-r)} in K/W 0,015 **IGBT** 0,01 0,005 0 0,0001 0,01 10000 t in s Fig. 6: Transient thermal impedance Zth(j-r)



R_{th} [K/W] 3 4 5 1 2 0,0055 0,0017 0,0007 0,0010 0,0049 Z_{th(j-s)} I Z_{th(j-s)} D 0,0020 0,0100 0,0112 0,0034 0,0015 0,0008 0,0020 0,0048 0,0023 th(j-r) D 0,0012 0,0039 0,0104 0,0054 0,0032 0,0014 0,0050 0,0001 $Z_{\mathsf{th}(\mathsf{s-a})}$ tau [s] 3 4 5 3,6500 0,4100 0,0650 0,0090 0,0008 _{th(j-s)} [′_{th(js)} D 3,6500 0,4100 0,0650 0,0090 0,0008 0,4500 0,0016 ∠_{th(j-r)} I 0,0475 0,0142 0,0107 $Z_{th(j-r)}D$ 4,1546 0,2644 0,0497 0,0005 34,2609 5,2284 0,0005 $Z_{th(s-a)}$

Fig. 8: Coefficients of thermal impedances

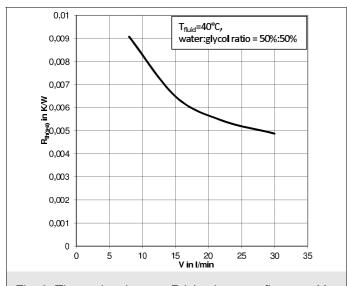


Fig. 9: Thermal resistance Rth(s-a) versus flow rate V

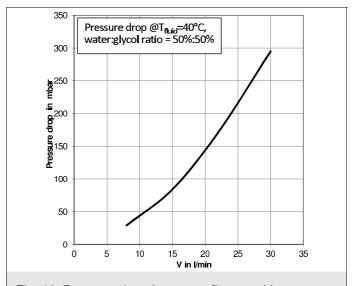
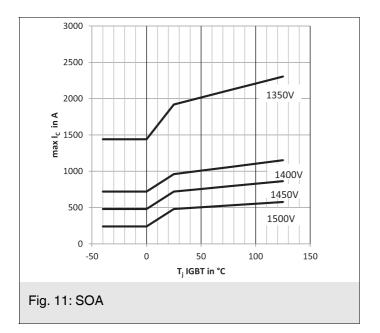
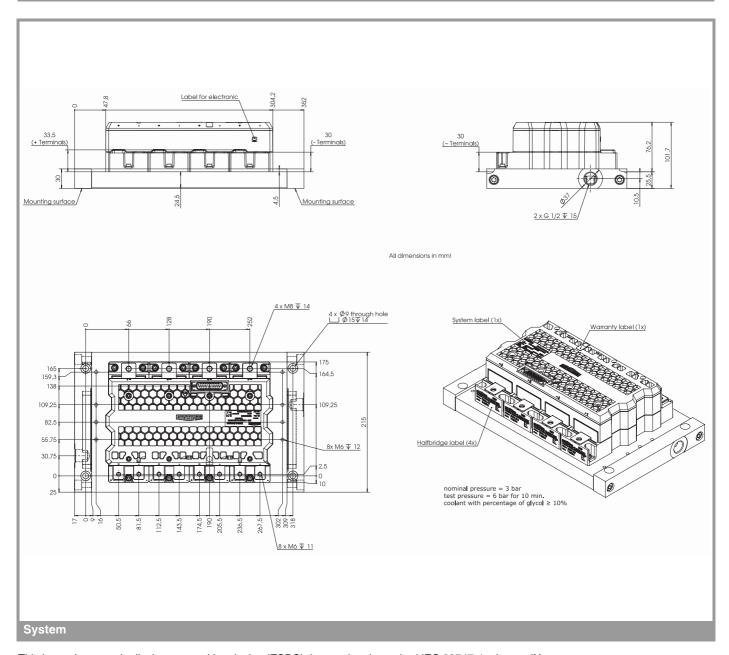


Fig. 10: Pressure drop Δp versus flow rate V





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

*IMPORTANT INFORMATION AND WARNINGS

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